

PROCESS CPQ090

TRIAC

4.0 Amp, 600 Volt TRIAC Chip

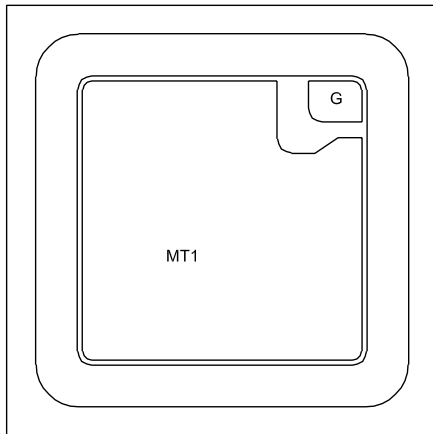
CentralTM
Semiconductor Corp.

www.DataSheet4U.com

PROCESS DETAILS

Process	Glass Passivated Mesa
Die Size	90 x 90 MILS
Die Thickness	8.6 MILS ± 0.6 MILS
MT1 Bonding Pad Area	61 x 48 MILS
Gate Bonding Pad Area	11 x 9.8 MILS
Top Side Metalization	Al - 45,000Å
Back Side Metalization	Al/Mo/Ni/Ag - 32,000Å

GEOMETRY



R0

BACKSIDE MT2

GROSS DIE PER 4 INCH WAFER

1,310

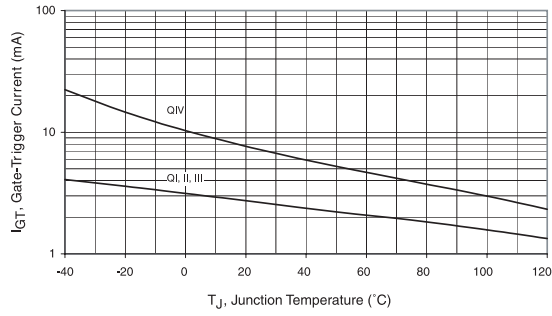
PRINCIPAL DEVICE TYPES

2N6075A
CQ202-4MS
CQ223-4M
CQD-4M

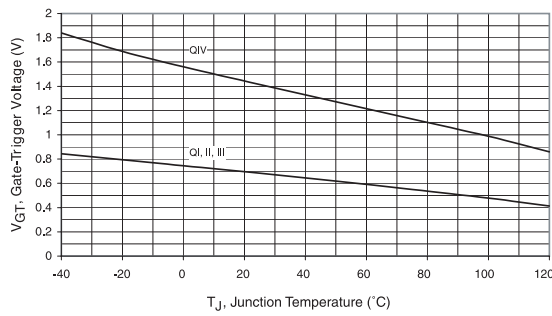
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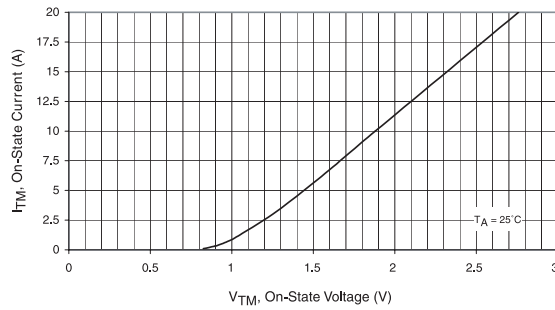
Typical Gate-Trigger Current



Typical Gate-Trigger Voltage



Typical On-State Voltage



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